

MM54HC365/MM74HC365 Hex TRI-STATE® Buffer **MM54HC366/MM74HC366 Inverting Hex TRI-STATE Buffer** **MM54HC367/MM74HC367 Hex TRI-STATE Buffer** **MM54HC368/MM74HC368 Inverting Hex TRI-STATE Buffer**

General Description

These TRI-STATE buffers are general purpose high speed inverting and non-inverting buffers that utilize advanced silicon-gate CMOS technology. They have high drive current outputs which enable high speed operation even when driving large bus capacitances. These circuits possess the low power dissipation of CMOS circuitry, yet have speeds comparable to low power Schottky TTL circuits. All 4 circuits are capable of driving up to 15 low power Schottky inputs.

The MM54/74HC366 and the MM54/74HC368 are inverting buffers, whereas the MM54/74HC365 and the MM54/74HC367 are non-inverting buffers. The MM54/74HC365 and the MM54/74HC366 have two TRI-STATE control inputs ($\overline{G1}$ and $\overline{G2}$) which are NORed together to control all

six gates. The MM54/74HC367 and the MM54/74HC368 also have two output enables, but one enable ($\overline{G1}$) controls 4 gates and the other ($\overline{G2}$) controls the remaining 2 gates.

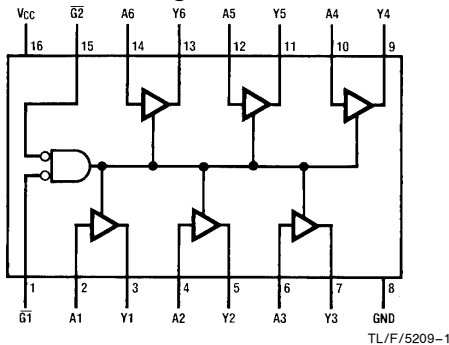
All inputs are protected from damage due to static discharge by diodes to V_{CC} and ground.

Features

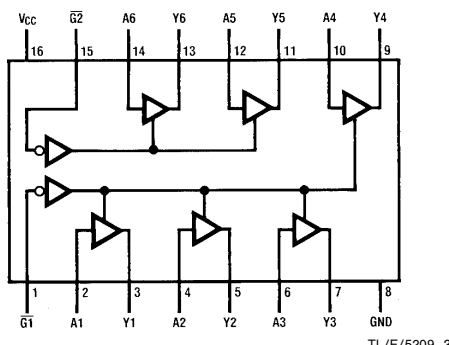
- Typical propagation delay: 15 ns
- Wide operating voltage range: 2V–6V
- Low input current: 1 μ A maximum
- Low quiescent current: 80 μ A maximum (74 Series)
- Output drive capability: 15 LS-TTL loads

Connection Diagrams

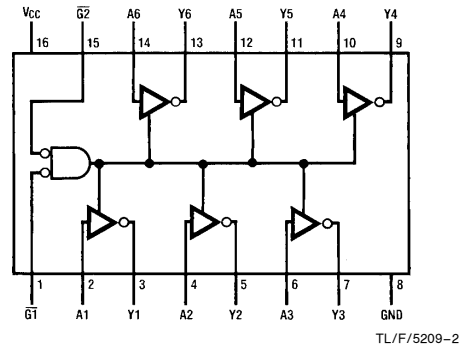
Dual-In-Line Packages/Top Views



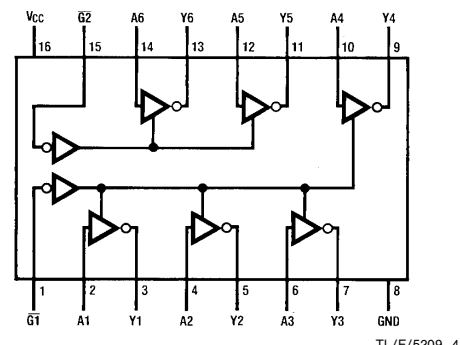
Order Number MM54HC365 or MM74HC365



Order Number MM54HC367 or MM74HC367



Order Number MM54HC366 or MM74HC366



Order Number MM54HC368 or MM74HC368

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Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V_{CC})	−0.5 to +7.0V
DC Input Voltage (V_{IN})	−1.5 to $V_{CC} + 1.5V$
DC Output Voltage (V_{OUT})	−0.5 to $V_{CC} + 0.5V$
Clamp Diode Current (I_{IK}, I_{OK})	±20 mA
DC Output Current, per pin (I_{OUT})	±35 mA
DC V_{CC} or GND Current, per pin (I_{CC})	±70 mA
Storage Temperature Range (T_{STG})	−65°C to +150°C
Power Dissipation (P_D)	
(Note 3)	600 mW
S.O. Package only	500 mW
Lead Temp. (T_L) (Soldering 10 seconds)	260°C

Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})	2	6	V
DC Input or Output Voltage (V_{IN}, V_{OUT})	0	V_{CC}	V
Operating Temp. Range (T_A)			
MM74HC	−40	+85	°C
MM54HC	−55	+125	°C
Input Rise or Fall Times (t_r, t_f)			
$V_{CC} = 2.0V$		1000	ns
$V_{CC} = 4.5V$		500	ns
$V_{CC} = 6.0V$		400	ns

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	V _{CC}	T _A = 25°C		74HC	54HC	Units
						T _A = −40 to 85°C	T _A = −55 to 125°C	
				Typ	Guaranteed Limits			
V _{IH}	Minimum High Level Input Voltage		2.0V		1.5	1.5	1.5	V
			4.5V		3.15	3.15	3.15	V
			6.0V		4.2	4.2	4.2	V
V _{IL}	Maximum Low Level Input Voltage**		2.0V		0.5	0.5	0.5	V
			4.5V		1.35	1.35	1.35	V
			6.0V		1.8	1.8	1.8	V
V _{OH}	Minimum High Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OUT} ≤ 20 μA	2.0V	2.0	1.9	1.9	1.9	V
			4.5V	4.5	4.4	4.4	4.4	V
			6.0V	6.0	5.9	5.9	5.9	V
		V _{IN} = V _{IH} or V _{IL} I _{OUT} ≤ 6.0 mA I _{OUT} ≤ 7.8 mA	4.5V	4.2	3.98	3.84	3.7	V
			6.0V	5.7	5.48	5.34	5.2	V
V _{OL}	Maximum Low Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OUT} ≤ 20 μA	2.0V	0	0.1	0.1	0.1	V
			4.5V	0	0.1	0.1	0.1	V
			6.0V	0	0.1	0.1	0.1	V
		V _{IN} = V _{IH} or V _{IL} I _{OUT} ≤ 6.0 mA I _{OUT} ≤ 7.8 mA	4.5V	0.2	0.26	0.33	0.4	V
			6.0V	0.2	0.26	0.33	0.4	V
I _{IN}	Maximum Input Current	V _{IN} = V _{CC} or GND	6.0V		±0.1	±1.0	±1.0	μA
I _{OZ}	Maximum TRI-STATE Output Leakage Current	V _{OUT} = V _{CC} or GND G̅ = V _{IH}	6.0V		±0.5	±5.0	±10	μA
I _{CC}	Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND I _{OUT} = 0 μA	6.0V		8.0	80	160	μA

Note 1: Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic “N” package: −12 mW/°C from 65°C to 85°C; ceramic “J” package: −12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of 5V ±10% the worst case output voltages (V_{OH} , and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at $V_{CC} = 5.5V$ and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN} , I_{CC} , and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

** V_{IL} limits are currently tested at 20% of V_{CC} . The above V_{IL} specification (30% of V_{CC}) will be implemented no later than Q1, CY'89.

AC Electrical Characteristics MM54HC365/MM74HC365

$V_{CC}=5V$, $T_A=25^{\circ}C$, $t_r=t_f=6\text{ ns}$

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t_{PHL} , t_{PLH}	Maximum Propagation Delay	$C_L = 45\text{ pF}$	15	22	ns
t_{PZH} , t_{PZL}	Maximum Output Enable Time	$R_L = 1\text{ k}\Omega$ $C_L = 45\text{ pF}$	29	40	ns
t_{PHZ} , t_{PLZ}	Maximum Output Disable Time	$R_L = 1\text{ k}\Omega$ $C_L = 5\text{ pF}$	25	36	ns

AC Electrical Characteristics MM54HC365/MM74HC365

$V_{CC}=2.0\text{--}6.0V$, $C_L=50\text{ pF}$, $t_r=t_f=6\text{ ns}$ (unless otherwise specified)

Symbol	Parameter	Conditions	V _{CC}	T _A = 25°C		74HC T _A = − 40 to 85°C	54HC T _A = − 55 to 125°C	Units
				Typ	Guaranteed Limits			
t _{PHL} , t _{PLH}	Maximum Propagation Delay	C _L = 50 pF	2.0V	35	105	130	150	ns
		C _L = 150 pF	2.0V	45	135	168	205	ns
		C _L = 50 pF	4.5V	14	24	30	36	ns
		C _L = 150 pF	4.5V	17	29	36	45	ns
		C _L = 50 pF	6.0V	11	19	24	28	ns
		C _L = 150 pF	6.0V	15	24	30	36	ns
t _{PZH} , t _{PZL}	Maximum Output Enable Time	R _L = 1 kΩ						
		C _L = 50 pF	2.0V	90	230	287	345	ns
		C _L = 150 pF	2.0V	98	245	306	367	ns
		C _L = 50 pF	4.5V	31	44	55	66	ns
		C _L = 150 pF	4.5V	38	53	66	80	ns
		C _L = 50 pF	6.0V	25	35	43	52	ns
		C _L = 150 pF	6.0V	29	41	51	62	ns
t _{PHZ} , t _{PLZ}	Maximum Output Disable Time	R _L = 1 kΩ	2.0V	58	175	218	260	ns
		C _L = 50 pF	4.5V	26	44	55	66	ns
			6.0V	22	37	46	55	ns
t _{THL} , t _{TLH}	Maximum Output Rise and Fall Time	C _L = 50 pF	2.0V	25	60	75	90	ns
			4.5V	7	12	15	18	ns
			6.0V	6	10	13	15	ns
C _{PD}	Power Dissipation Capacitance (Note 5)	Any Enabled A Input		45				pF
		Any Disabled A Input		8				pF
C _{IN}	Maximum Input Capacitance			5	10	10	10	pF
C _{OUT}	Maximum Output Capacitance			10	20	20	20	pF

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.

Truth Table

'HC365

Inputs			Output
$\overline{G1}$	$\overline{G2}$	A	
H	X	X	Z
X	H	X	Z
L	L	H	H
L	L	L	L

AC Electrical Characteristics (Continued) MM54HC366/MM74HC366

$V_{CC} = 5V$, $T_A = 25^\circ C$, $t_r = t_f = 6$ ns

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t_{PHL} , t_{PLH}	Maximum Propagation Delay	$C_L = 45$ pF	12	18	ns
t_{PZL} , t_{PZH}	Maximum Output Enable Time	$R_L = 1$ k Ω $C_L = 45$ pF	29	40	ns
t_{PHZ} , t_{PLZ}	Maximum Output Disable Time	$R_L = 1$ k Ω $C_L = 5$ pF	25	36	ns

AC Electrical Characteristics MM54HC366/MM74HC366

$V_{CC} = 2.0$ – $6.0V$, $C_L = 50$ pF, $t_r = t_f = 6$ ns (unless otherwise specified)

Symbol	Parameter	Conditions	V _{CC}	T _A = 25°C		74HC T _A = −40 to 85°C	54HC T _A = −55 to 125°C	Units
				Typ	Guaranteed Limits			
t _{PHL} , t _{PLH}	Maximum Propagation Delay	C _L = 50 pF	2.0V	33	82	102	125	ns
		C _L = 150 pF	2.0V	43	107	134	160	ns
		C _L = 50 pF	4.5V	12	19	24	30	ns
		C _L = 150 pF	4.5V	16	26	32	39	ns
		C _L = 50 pF	6.0V	10	16	20	24	ns
		C _L = 150 pF	6.0V	14	22	27	33	ns
t _{PZH} , t _{PZL}	Maximum Output Enable Time	R _L = 1 kΩ						ns
		C _L = 50 pF	2.0V	90	230	287	345	ns
		C _L = 150 pF	2.0V	98	245	306	367	ns
		C _L = 50 pF	4.5V	31	44	55	66	ns
		C _L = 150 pF	4.5V	38	53	66	80	ns
		C _L = 50 pF	6.0V	25	35	43	52	ns
t _{PHZ} , t _{PLZ}	Maximum Output Disable Time	C _L = 150 pF	6.0V	29	41	51	62	ns
		R _L = 1 kΩ	2.0V	58	175	218	260	ns
		C _L = 50 pF	4.5V	26	44	55	66	ns
			6.0V	22	37	46	55	ns
t _{THL} , t _{TLH}	Maximum Output Rise and Fall Time	C _L = 50 pF	2.0V	25	60	75	90	ns
			4.5V	7	12	15	18	ns
		6.0V	6	10	13	15	ns	
C _{PD}	Power Dissipation Capacitance (Note 5)	Any Enabled A Input		45				pF
		Any Disabled A Input		6				pF
C _{IN}	Maximum Input Capacitance			5	10	10	10	pF
C _{OUT}	Maximum Output Capacitance			10	20	20	20	pF

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.

Truth Table

'HC366

Inputs			Output
$\overline{G1}$	$\overline{G2}$	A	Y
H	X	X	Z
X	H	X	Z
L	L	H	L
L	L	L	H

AC Electrical Characteristics (Continued) MM54HC367/MM74HC367

$V_{CC}=5V$, $T_A=25^{\circ}C$, $t_r=t_f=6\text{ ns}$

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t_{PHL} , t_{PLH}	Maximum Propagation Delay	$C_L = 45\text{ pF}$	13	22	ns
t_{PZL} , t_{PZH}	Maximum Output Enable Time	$R_L = 1\text{ k}\Omega$ $C_L = 45\text{ pF}$	23	37	ns
t_{PHZ} , t_{PLZ}	Maximum Output Disable Time	$R_L = 1\text{ k}\Omega$ $C_L = 5\text{ pF}$	25	33	ns

AC Electrical Characteristics MM54HC367/MM74HC367

$V_{CC}=2.0\text{--}6.0V$, $C_L=50\text{ pF}$, $t_r=t_f=6\text{ ns}$ (unless otherwise specified)

Symbol	Parameter	Conditions	V _{CC}	T _A = 25°C		74HC T _A = − 40 to 85°C	54HC T _A = − 55 to 125°C	Units
				Typ	Guaranteed Limits			
t _{PHL} , t _{PLH}	Maximum Propagation Delay	C _L = 50 pF	2.0V	35	105	130	150	ns
		C _L = 150 pF	2.0V	45	135	168	205	ns
		C _L = 50 pF	4.5V	14	24	30	36	ns
		C _L = 150 pF	4.5V	17	29	36	45	ns
		C _L = 50 pF	6.0V	11	19	24	28	ns
		C _L = 150 pF	6.0V	15	24	30	36	ns
t _{PZH} , t _{PZL}	Maximum Output Enable Time	R _L = 1 kΩ						ns
		C _L = 50 pF	2.0V	69	172	216	250	ns
		C _L = 150 pF	2.0V	75	187	233	280	ns
		C _L = 50 pF	4.5V	24	38	47	57	ns
		C _L = 150 pF	4.5V	29	46	57	69	ns
		C _L = 50 pF	6.0V	22	35	43	52	ns
C _L = 150 pF	6.0V	26	42	52	63	ns		
t _{PHZ} , t _{PLZ}	Maximum Output Disable Time	R _L = 1 kΩ	2.0V	47	117	146	220	ns
		C _L = 50 pF	4.5V	22	35	44	52	ns
			6.0V	19	31	39	46	ns
t _{THL} , t _{TLH}	Maximum Output Rise and Fall Time	C _L = 50 pF	2.0V	25	60	75	90	ns
			4.5V	7	12	15	18	ns
			6.0V	6	10	13	15	ns
C _{PD}	Power Dissipation Capacitance (Note 5)	Any Enabled A Input		45				pF
		Any Disabled A Input		8				pF
C _{IN}	Maximum Input Capacitance			5	10	10	10	pF
C _{OUT}	Maximum Output Capacitance			10	20	20	20	pF

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.

Truth Table

'HC367

Inputs		Output
$\bar{G}$	A	Y
H	X	Z
L	H	H
L	L	L

AC Electrical Characteristics (Continued) MM54HC368/MM74HC368

$V_{CC} = 5V$, $T_A = 25^\circ C$, $t_r = t_f = 6$ ns

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t_{PHL} , t_{PLH}	Maximum Propagation Delay	$C_L = 45$ pF	11	18	ns
t_{PZL} , t_{PZH}	Maximum Output Enable Time	$R_L = 1$ k Ω $C_L = 45$ pF	23	37	ns
t_{PHZ} , t_{PLZ}	Maximum Output Disable Time	$R_L = 1$ k Ω $C_L = 5$ pF	19	33	ns

AC Electrical Characteristics MM54HC368/MM74HC368

$V_{CC} = 2.0$ – $6.0V$, $C_L = 50$ pF, $t_r = t_f = 6$ ns (unless otherwise specified)

Symbol	Parameter	Conditions	V_{CC}	$T_A = 25^\circ C$		74HC $T_A = -40$ to $85^\circ C$	54HC $T_A = -55$ to $125^\circ C$	Units
				Typ	Guaranteed Limits			
t_{PHL} , t_{PLH}	Maximum Propagation Delay	$C_L = 50$ pF	2.0V	33	82	102	125	ns
		$C_L = 150$ pF	2.0V	43	107	134	160	ns
		$C_L = 50$ pF	4.5V	12	19	24	30	ns
		$C_L = 150$ pF	4.5V	16	26	32	39	ns
		$C_L = 50$ pF	6.0V	10	16	20	24	ns
		$C_L = 150$ pF	6.0V	14	22	27	33	ns
t_{PZH} , t_{PZL}	Maximum Output Enable Time	$R_L = 1$ k Ω						ns
		$C_L = 50$ pF	2.0V	69	172	216	250	ns
		$C_L = 150$ pF	2.0V	75	187	233	280	ns
		$C_L = 50$ pF	4.5V	24	38	47	57	ns
		$C_L = 150$ pF	4.5V	29	46	57	69	ns
		$C_L = 50$ pF	6.0V	22	35	43	52	ns
t_{PHZ} , t_{PLZ}	Maximum Output Disable Time	$R_L = 1$ k Ω	2.0V	47	117	146	220	ns
		$C_L = 50$ pF	4.5V	22	35	44	52	ns
			6.0V	19	31	39	46	ns
t_{THL} , t_{TLH}	Maximum Output Rise and Fall Time	$C_L = 50$ pF	2.0V	25	60	75	90	ns
			4.5V	7	12	15	18	ns
			6.0V	6	10	13	15	ns
C_{PD}	Power Dissipation Capacitance (Note 5)	Any Enabled A Input		45				pF
		Any Disabled A Input		6				pF
C_{IN}	Maximum Input Capacitance			5	10	10	10	pF
C_{OUT}	Maximum Input Capacitance			10	20	20	20	pF

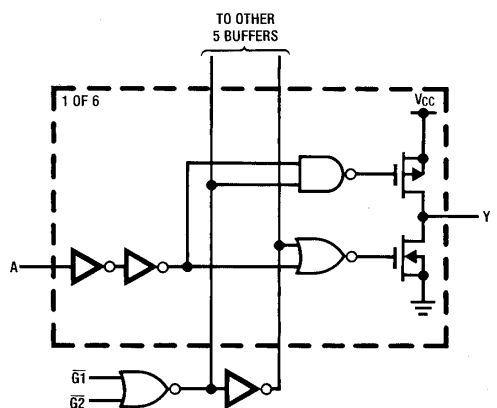
Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.

Truth Table

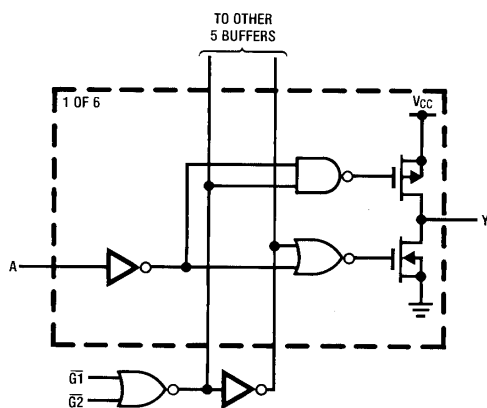
'HC368

Inputs		Output Y
$\bar{G}$	A	
H	X	Z
L	H	L
L	L	H

Logic Diagrams

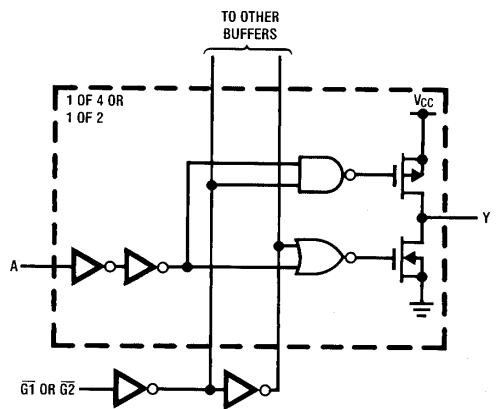
MM54HC365/MM74HC365

TL/F/5209-5

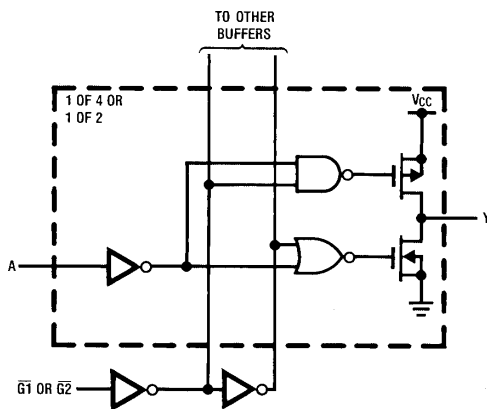
MM54HC366/MM74HC366

TL/F/5209-6

MM54HC367/MM74HC367

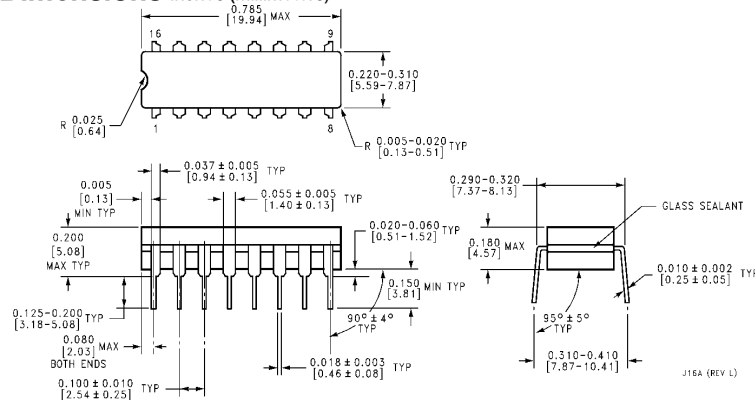


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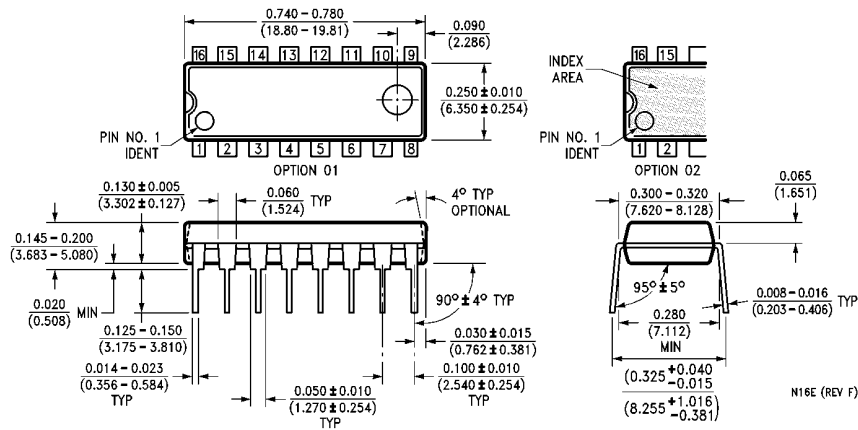
MM54HC368/MM74HC368

TL/F/5209-8

Physical Dimensions inches (millimeters)



Order Number MM54HC365J, MM54HC366J, MM54HC367J, MM54HC368J,
MM74HC365J, MM74HC366J, MM74HC367J, or MM74HC368J,
NS Package J16A



Order Number MM74HC365N, MM74HC366N, MM74HC367N, or MM74HC368N
NS Package N16E

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National Semiconductor Corporation
1111 West Bardin Road
Arlington, TX 76017
Tel: 1(800) 272-9959
Fax: 1(800) 737-7018

National Semiconductor Europe
Fax: (+49) 0-180-530 85 86
Email: onjwge@tevm2.nsc.com
Deutsch Tel: (+49) 0-180-530 85 85
English Tel: (+49) 0-180-532 78 32
Français Tel: (+49) 0-180-532 93 58
Italiano Tel: (+49) 0-180-534 16 80

National Semiconductor Hong Kong Ltd.
19th Floor, Straight Block,
Ocean Centre, 5 Canton Rd.
Tsimshatsui, Kowloon
Hong Kong
Tel: (852) 2737-1600
Fax: (852) 2736-9960

National Semiconductor Japan Ltd.
Tel: 81-043-299-2309
Fax: 81-043-299-2408

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В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9